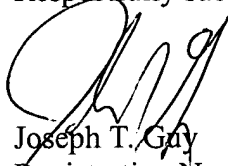


Respectfully submitted,



Joseph T. Gay

Registration No. 35,172

Agent for Applicant

NEXSEN PRUET JACOBS & POLLARD, LLC

201 West McBee Avenue

Suite 400

Greenville, SC 29601

Telephone: 864-370-2211

Facsimile: 864-282-1177

January 16, 2002

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APPENDIX A -Claim Amendments

Please amend claims 3, 5 and 7 in accordance with the following instructions.

A₁ 3.(Amended) A method according to claim 1 [or 2] wherein said copper ions are copper (I) ions.

A₂ 5.(Amended) A method according to any of [claims 1 to 4] claim 1 further comprising the step of
subjecting the mixture formed by said precipitation step to a diafiltration and/or
ultrafiltration treatment.

A₃ 7.(Amended) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer
containing ZnS:Cu particles prepared by a method according to [any of the previous
claims] claim 1.

Please enter claims 8-29 as indicated.

A₄ 8.(New) A method according to claim 2 wherein said copper ions are copper (I) ions.

9.(New) A method according to claim 8 wherein said copper (I) ions are incorporated as
copper (I) chloride.

10.(New) A method according to any of claim 2 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.

11.(New) A method according to claim 10 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.

12.(New) A method according to any of claim 3 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.

13.(New) A method according to claim 12 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.

14.(New) A method according to any of claim 4 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.

15.(New) A method according to claim 14 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.

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- 16.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 2.
- 17.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 3.
- 18.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 4.
- 19.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 5.
- 20.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 6.
- 21.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 7.
- 22.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 8.
- 23.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 9.

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- 24.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 10.
- 25.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 11.
- 26.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 12.
- 27.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 13.
- 28.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 14.
- 29.(New) A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 15.